

Radiation Hardened Triple 3-Input AND Gate

November 1994

Features

- 3 Micron Radiation Hardened SOS CMOS
- Total Dose 200K or 1 Mega-RAD(Si)
- Dose Rate Upset $>10^{10}$ RAD(Si)/s 20ns Pulse
- Cosmic Ray Upset Immunity $< 2 \times 10^{-9}$ Errors/Gate Day (Typ)
- Latch-Up Free Under Any Conditions
- Military Temperature Range: -55°C to $+125^{\circ}\text{C}$
- Significant Power Reduction Compared to LSTTL ICs
- DC Operating Voltage Range: 4.5V to 5.5V
- Input Logic Levels
 - $V_{IL} = 30\%$ of VCC Max
 - $V_{IH} = 70\%$ of VCC Min
- Input Current Levels $I_i \leq 5\mu\text{A}$ at VOL, VOH

Description

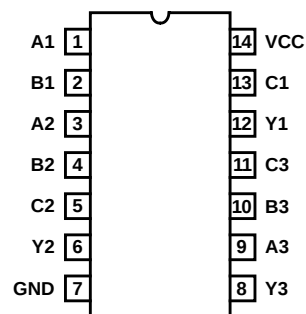
The Intersil HCS11MS is a Radiation Hardened Triple 3-Input AND Gate. A high on all inputs forces the output to a High state.

The HCS11MS utilizes advanced CMOS/SOS technology to achieve high-speed operation. This device is a member of radiation hardened, high-speed, CMOS/SOS Logic Family.

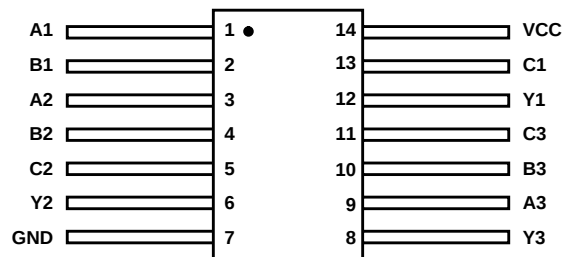
The HCS11MS is supplied in a 14 lead Weld Seal Ceramic flatpack (K suffix) or a Weld Seal Ceramic Dual-In-Line Package (D suffix).

Pinouts

14 PIN CERAMIC DUAL-IN-LINE
MIL-STD-1835 DESIGNATOR CDIP2-T14, LEAD FINISH C
TOP VIEW



14 PIN CERAMIC FLAT PACK
MIL-STD-1835 DESIGNATOR CDFP3-F14, LEAD FINISH C
TOP VIEW

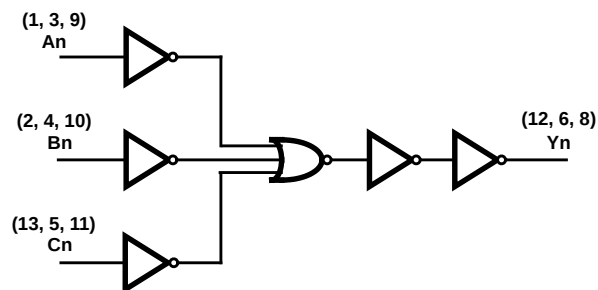


Truth Table

INPUTS			OUTPUTS
An	Bn	Cn	Yn
L	L	L	L
L	L	H	L
L	H	L	L
L	H	H	L
H	L	L	L
H	L	H	L
H	H	L	L
H	H	H	H

NOTE: L = Logic Level Low, H = Logic level High

Functional Diagram



Specifications HCS11MS

Absolute Maximum Ratings

Supply Voltage -0.5V to +7.0V
 Input Voltage Range, All Inputs -0.5V to VCC +0.5V
 DC Input Current, Any One Input $\pm 10\text{mA}$
 DC Drain Current, Any One Output $\pm 25\text{mA}$
 (All Voltage Reference to the VSS Terminal)
 Storage Temperature Range (TSTG) -65°C to +150°C
 Lead Temperature (Soldering 10sec) +265°C
 Junction Temperature (TJ) +175°C
 ESD Classification Class 1

Reliability Information

Thermal Impedance θ_{ja} θ_{jc}
 Weld Seal DIC 75°C/W 16°C/W
 Weld Seal Flat Pack 64°C/W 12°C/W
 Power Dissipation per Package (PD)
 For T_A = -55°C to +100°C 1W
 For T_A = +100°C to +125°C Derate Linearly at 13mW/°C

CAUTION: As with all semiconductors, stress listed under "Absolute Maximum Ratings" may be applied to devices (one at a time) without resulting in permanent damage. This is a stress rating only. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. The conditions listed under "Electrical Performance Characteristics" are the only conditions recommended for satisfactory device operation..

Operating Conditions

Supply Voltage +4.5V to +5.5V
 Input Rise and Fall Times at 4.5V VCC (TR, TF) 100ns/V Max
 Operating Temperature Range (T_A) -55°C to +125°C
 Input Low Voltage (VIL) 0.0V to 30% of VCC
 Input High Voltage (VIH) 70% of VCC to VCC

TABLE 1. DC. ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETERS	SYMBOL	(NOTE 1) CONDITIONS	GROUP A SUB- GROUPS	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Quiescent Current	ICC	VCC = 5.5V, VIN = VCC or GND	1	+25°C	-	10	μA
			2, 3	+125°C, -55°C	-	200	μA
Output Current (Sink)	IOL	VCC = 4.5V, VIH = 4.5V, VOUT = 0.4V, VIL = 0V	1	+25°C	4.8	-	mA
			2, 3	+125°C, -55°C	4.0	-	mA
Output Current (Source)	IOH	VCC = 4.5V, VIH = 4.5V, VOUT = VCC -0.4V, VIL = 0V	1	+25°C	-4.8	-	mA
			2, 3	+125°C, -55°C	-4.0	-	mA
Output Voltage Low	VOL	VCC = 4.5V, VIH = 3.15V, IOL = 50μA, VIL = 1.35V	1, 2, 3	+25°C, +125°C, -55°C	-	0.1	V
		VCC = 5.5V, VIH = 3.85V, IOL = 50μA, VIL = 1.65V	1, 2, 3	+25°C, +125°C, -55°C	-	0.1	V
Output Voltage High	VOH	VCC = 4.5V, VIH = 3.15V, IOH = -50μA, VIL = 1.35V	1, 2, 3	+25°C, +125°C, -55°C	VCC -0.1	-	V
		VCC = 5.5V, VIH = 3.85V, IOH = -50μA, VIL = 1.65V	1, 2, 3	+25°C, +125°C, -55°C	VCC -0.1	-	V
Input Leakage Current	IIN	VCC = 5.5V, VIN = VCC or GND	1	+25°C	-	±0.5	μA
			2, 3	+125°C, -55°C	-	±5.0	μA
Noise Immunity Functional Test	FN	VCC = 4.5V, VIH = 0.70(VCC), VIL = 0.30(VCC) (Note 2)	7, 8A, 8B	+25°C, +125°C, -55°C	-	-	-

NOTE:

1. All voltages reference to device GND.
2. For functional tests VO ≥ 4.0V is recognized as a logic "1", and VO ≤ 0.5V is recognized as a logic "0".

All Intersil semiconductor products are manufactured, assembled and tested under **ISO9000** quality systems certification.

Intersil products are sold by description only. Intersil Corporation reserves the right to make changes in circuit design and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that data sheets are current before placing orders. Information furnished by Intersil is believed to be accurate and reliable. However, no responsibility is assumed by Intersil or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Intersil or its subsidiaries.

For information regarding Intersil Corporation and its products, see web site <http://www.intersil.com>

Specifications HCS11MS

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	(NOTES 1, 2) CONDITIONS	GROUP A SUB- GROUPS	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Input to Yn	TPHL	VCC = 4.5V	9	+25°C	2	18	ns
			10, 11	+125°C, -55°C	2	20	ns
Input to Yn	TPLH	VCC = 4.5V	9	+25°C	2	20	ns
			10, 11	+125°C, -55°C	2	22	ns

NOTES:

1. All voltages referenced to device GND.
2. AC measurements assume $R_L = 500\Omega$, $C_L = 50\text{pF}$, Input $T_R = T_F = 3\text{ns}$, $V_{IL} = \text{GND}$, $V_{IH} = V_{CC}$.

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Capacitance Power Dissipation	CPD	VCC = 5.0V, $f = 1\text{MHz}$	1	+25°C	Typical 20		pF
			1	+125°C	Typical 30		pF
Input Capacitance	CIN	VCC = Open, $f = 1\text{MHz}$	1	+25°C	-	10	pF
			1	+125°C	-	10	pF
Output Transition Time	TTHL TTLH	VCC = 4.5V	1	+25°C	-	15	ns
			1	+125°C	-	22	ns

NOTE:

1. The parameters listed in Table 3 are controlled via design or process parameters. Min and Max Limits are guaranteed but not directly tested. These parameters are characterized upon initial design release and upon design changes which affect these characteristics.

TABLE 4. DC POST RADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETERS	SYMBOL	(NOTES 1, 2) CONDITIONS	TEMP- ERATURE	200K RAD LIMITS		1M RAD LIMITS		UNITS
				MIN	MAX	MIN	MAX	
Quiescent Current	ICC	VCC = 5.5V, $V_{IN} = V_{CC}$ or GND	+25°C	-	0.2	-	1.0	mA
Output Current (Sink)	IOL	VCC = 4.5V, $V_{IN} = V_{CC}$ or GND, $V_{OUT} = 0.4\text{V}$	+25°C	4.0	-	4.0	-	mA
Output Current (Source)	IOH	VCC = 4.5V, $V_{IN} = V_{CC}$ or GND, $V_{OUT} = V_{CC} - 0.4\text{V}$	+25°C	-4.0	-	-4.0	-	mA
Output Voltage Low	VOL	VCC = 4.5V and 5.5V, $V_{IH} = 0.70(V_{CC})$, $V_{IL} = 0.30(V_{CC})$ at 200K RAD, $V_{IL} = 0.12(V_{CC})$ at 1M RAD, $I_{OL} = 50\mu\text{A}$	+25°C	-	0.1	-	0.1	V
Output Voltage High	VOH	VCC = 4.5V and 5.5V, $V_{IH} = 0.70(V_{CC})$, $V_{IL} = 0.30(V_{CC})$ at 200K RAD, $V_{IL} = 0.12(V_{CC})$ at 1M RAD, $I_{OH} = -50\mu\text{A}$	+25°C	VCC - 0.1	-	VCC - 0.1	-	V
Input Leakage Current	IIN	VCC = 5.5V, $V_{IN} = V_{CC}$ or GND	+25°C	-	±5	-	±5	μA
Noise Immunity Functional Test	FN	VCC = 4.5V, $V_{IH} = 0.70(V_{CC})$, $V_{IL} = 0.30(V_{CC})$ at 200K RAD, $V_{IL} = 0.12(V_{CC})$ at 1M RAD (Note 3)	+25°C	-	-	-	-	-

Specifications HCS11MS

TABLE 4. DC POST RADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

PARAMETERS	SYMBOL	(NOTES 1, 2) CONDITIONS	TEMP- ERATURE	200K RAD LIMITS		1M RAD LIMITS		UNITS
				MIN	MAX	MIN	MAX	
Data to Output	TPHL	VCC = 4.5V	+25°C	2	20	2	25	ns
	TPLH	VCC = 4.5V	+25°C	2	22	2	28	ns

NOTES:

1. All voltages referenced to device GND.
2. AC measurements assume $R_L = 500\Omega$, $C_L = 50\text{pF}$, Input $T_R = T_F = 3\text{ns}$, $V_{IL} = \text{GND}$, $V_{IH} = V_{CC}$.
3. For functional tests $V_O \geq 4.0\text{V}$ is recognized as a logic "1", and $V_O \leq 0.5\text{V}$ is recognized as a logic "0".

TABLE 5. BURN-IN AND OPERATING LIFE TEST, DELTA PARAMETERS (+25°C)

PARAMETER	GROUP B SUBGROUP	DELTA LIMIT
ICC	5	3 μA
IOL/IOH	5	-15% of 0 Hour

TABLE 6. APPLICABLE SUBGROUPS

CONFORMANCE GROUPS		METHOD	GROUP A SUBGROUPS	READ AND RECORD
Initial Test (Preburn-In)		100%/5004	1, 7, 9	ICC, IOL/H
Interim Test I (Postburn-In)		100%/5004	1, 7, 9	ICC, IOL/H
Interim Test II (Postburn-In)		100%/5004	1, 7, 9	ICC, IOL/H
PDA		100%/5004	1, 7, 9, Deltas	
Interim Test III (Postburn-In)		100%/5004	1, 7, 9	ICC, IOL/H
PDA		100%/5004	1, 7, 9, Deltas	
Final Test		100%/5004	2, 3, 8A, 8B, 10, 11	
Group A (Note 1)		Sample/5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11	
Group B	Subgroup B-5	Sample/5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11, Deltas	Subgroups 1, 2, 3, 9, 10, 11
	Subgroup B-6	Sample/5005	1, 7, 9	
Group D		Sample/5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11	

NOTE:

1. Alternate group A inspection in accordance with method 5005 of MIL-STD-883 may be exercised.

TABLE 7. TOTAL DOSE IRRADIATION

CONFORMANCE GROUPS	METHOD	TEST		READ AND RECORD	
		PRE RAD	POST RAD	PRE RAD	POST RAD
Group E Subgroup 2	5005	1, 7, 9	Table 4	1, 9	Table 4 (Note 1)

NOTE:

1. Except FN test which will be performed 100% Go/No-Go.

TABLE 8. STATIC AND DYNAMIC BURN-IN TEST CONNECTIONS

OPEN	GROUND	1/2 VCC = 3V ± 0.5V	VCC = 6V ± 0.5V	OSCILLATOR	
				50kHz	25kHz
STATIC BURN-IN I TEST CONDITIONS (Note 1)					

Specifications HCS11MS

TABLE 8. STATIC AND DYNAMIC BURN-IN TEST CONNECTIONS

OPEN	GROUND	1/2 VCC = 3V ± 0.5V	VCC = 6V ± 0.5V	OSCILLATOR	
				50kHz	25kHz
6, 8, 12	1, 2, 3, 4, 5, 7, 9, 10, 11, 13	-	14	-	-
STATIC BURN-IN II TEST CONNECTIONS (Note 1)					
6, 8, 12	7	-	1, 2, 3, 4, 5, 9, 10, 11, 13, 14	-	-
DYNAMIC BURN-IN I TEST CONNECTIONS (Note 2)					
-	7	6, 8, 12	14	1, 2, 3, 4, 5, 9, 10, 11, 13	-

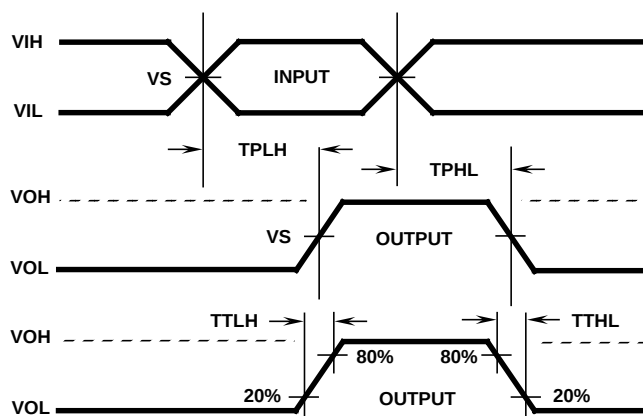
NOTES:

1. Each pin except VCC and GND will have a resistor of 10KΩ ± 5% for static burn-in.
2. Each pin except VCC and GND will have a resistor of 680KΩ ± 5% for dynamic burn-in.

TABLE 9. IRRADIATION TEST CONNECTIONS

OPEN	GROUND	VCC = 5V ± 0.5V
6, 8, 12	7	1, 2, 3, 4, 5, 9, 10, 11, 13, 14

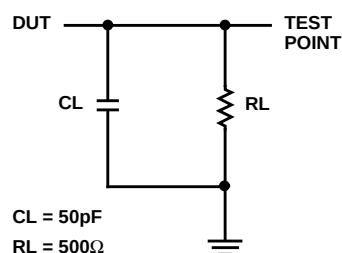
AC Timing Diagrams



AC VOLTAGE LEVELS

PARAMETER	HCS	UNITS
VCC	4.50	V
VIH	4.50	V
VS	2.25	V
VIL	0	V
GND	0	V

AC Load Circuit



HCS11MS

Die Characteristics

DIE DIMENSIONS:

87 x 88 mils
2.20 x 2.24mm

METALLIZATION:

Type: AlSi
Metal Thickness: $11\text{k}\text{\AA} \pm 1\text{k}\text{\AA}$

GLASSIVATION:

Type: SiO_2
Thickness: $13\text{k}\text{\AA} \pm 2.6\text{k}\text{\AA}$

DIE ATTACH:

Material: Silver Epoxy

WORST CASE CURRENT DENSITY:

$<2.0 \times 10^5 \text{A/cm}^2$

BOND PAD SIZE:

$100\mu\text{m} \times 100\mu\text{m}$
4 x 4 mils

Metallization Mask Layout

